

Complementary Plastic Silicon Power Transistors BD787G (NPN), BD788G (PNP)

4 AMPERES POWER TRANSISTORS COMPLEMENTARY SILICON 60 VOLTS, 15 WATTS

Description

These devices are designed for lower power audio amplifier and low current, high-speed switching applications.

Features

- Low Collector-Emitter Sustaining Voltage
- High Current-Gain Bandwidth Product
- These Devices are Pb-Free and are RoHS Compliant*

MAXIMUM RATINGS

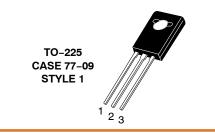
Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V _{CEO}	60	Vdc
Collector-Base Voltage	V _{CBO}	80	Vdc
Emitter Base Voltage	V _{EBO}	6.0	Vdc
Collector Current - Continuous	I _C	4.0	Adc
Collector Current - Peak	I _{CM}	8.0	Adc
Base Current - Continuous	Ι _Β	1.0	Adc
Total Power Dissipation @ T _C = 25°C Derate above 25°C	P _D	15 0.12	W mW/°C
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-65 to +150	°C

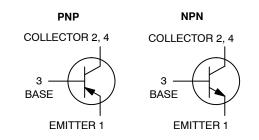
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

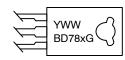
Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	8.34	°C/W

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MARKING DIAGRAM



ORDERING INFORMATION

Device	Package	Shipping
BD787G	TO-225 (Pb-Free)	500 Units/Box

DISCONTINUED (Note 1)

BD788G	TO-225 (Pb-Free)	500 Units/Box
	(FD-Flee)	

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

 DISCONTINUED: This device is not recommended for new design. Please contact your onsemi representative for information. The most current information on this device may be available on www.onsemi.com.

^{*}For additional information on our Pb-Free strategy and soldering details, please download the **onsemi** Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

ELECTRICAL CHARACTERISTICS* ($T_C = 25$ °C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS	<u> </u>			
Collector–Emitter Sustaining Voltage (Note 2) $(I_C = 10 \text{ mAdc}, I_B = 0)$	V _{CEO(sus)}	60	_	Vdc
Collector Cutoff Current $(V_{CE} = 20 \text{ Vdc}, I_B = 0)$ $(V_{CE} = 30 \text{ Vdc}, I_B = 0)$	I _{CEO}	-	100	μAdc
Collector Cutoff Current $(V_{CE} = 80 \text{ Vdc}, V_{BE(off)} = 1.5 \text{ Vdc})$ $(V_{CE} = 40 \text{ Vdc}, V_{BE(off)} = 1.5 \text{ Vdc}, T_C = 125^{\circ}C)$	I _{CEX}	- -	1.0 0.1	μAdc mAdc
Emitter Cutoff Current (V _{EB} = 6.0 Vdc, I _C = 0)	I _{EBO}	-	1.0	μAdc
ON CHARACTERISTICS (Note 2)	<u> </u>			
DC Current Gain ($I_C = 200 \text{ mAdc}$, $V_{CE} = 3.0 \text{ Vdc}$) ($I_C = 1.0 \text{ Adc}$, $V_{CE} = 3.0 \text{ Vdc}$) ($I_C = 2.0 \text{ Adc}$, $V_{CE} = 3.0 \text{ Vdc}$) ($I_C = 4.0 \text{ Adc}$, $V_{CE} = 3.0 \text{ Vdc}$)	h _{FE}	40 25 20 5.0	250 - - -	-
Collector–Emitter Saturation Voltage (I_C = 500 mAdc, I_B = 50 mAdc) (I_C = 1.0 Adc, I_B = 100 mAdc) (I_C = 2.0 Adc, I_B = 200 mAdc) (I_C = 4.0 Adc, I_B = 800 mAdc)	V _{CE(sat)}	- - - -	0.4 0.6 0.8 2.5	Vdc
Base–Emitter Saturation Voltage (I _C = 2.0 Adc, I _B = 200 mAdc)	V _{BE(sat)}	-	2.0	Vdc
Base–Emitter On Voltage ($I_C = 2.0$ Adc, $V_{CE} = 3.0$ Vdc)	V _{BE(on)}	-	1.8	Vdc
DYNAMIC CHARACTERISTICS				
Current-Gain - Bandwidth Product ($I_C = 100 \text{ mAdc}$, $V_{CE} = 10 \text{ Vdc}$, $f = 10 \text{ MHz}$)	f _T	50	-	MHz
Output Capacitance $(V_{CB} = 10 \text{ Vdc}, I_{C} = 0)$ BD787G	C _{ob}	-	50	pF
(f = 0.1 MHz) BD788G		-	70	
Small–Signal Current Gain ($I_C = 200$ mAdc, $V_{CE} = 10$ Vdc, $f = 1.0$ kHz)	h _{fe}	10	-	-

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.
*Indicates JEDEC Registered Data
2. Pulse Test; Pulse Width ≤ 300 µs, Duty Cycle ≤ 2.0%.

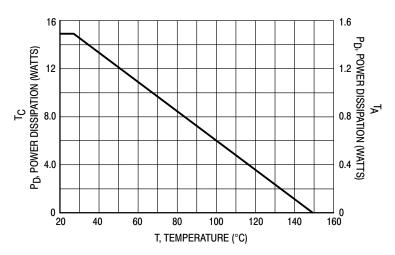


Figure 1. Power Derating

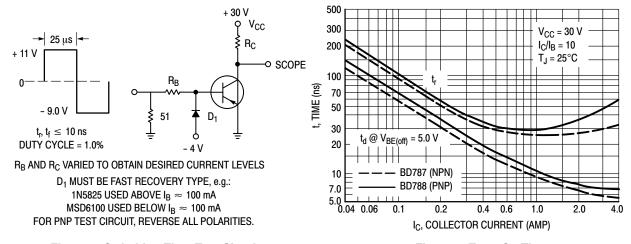


Figure 2. Switching Time Test Circuit

Figure 3. Turn-On Time

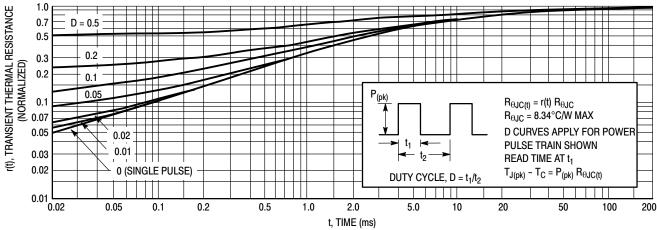


Figure 4. Thermal Response

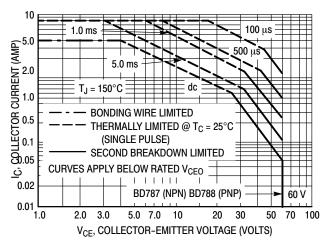


Figure 5. Active Region Safe Operating Area

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate I_C - V_{CE} limits of the transistor that must be observed for reliable operation, i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 5 is based on $T_{J(pk)} = 150^{\circ}\text{C}$: T_C is variable depending on conditions. Second breakdown pulse limits are valid for duty cycles to 10% provided T_{J(pk)} $\leq 150^{\circ}$ C, $T_{J(pk)}$ may be calculated from the data in Figure 4. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

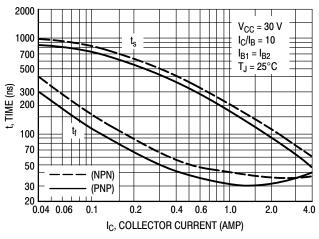


Figure 6. Turn-Off Time

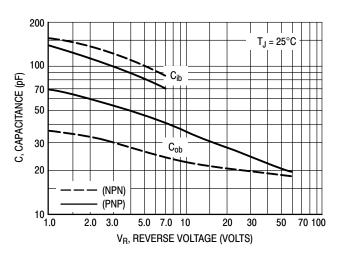


Figure 7. Capacitance

0.6

V_{CE} = 1.0 V

V_{CE} = 3.0 V

2.0

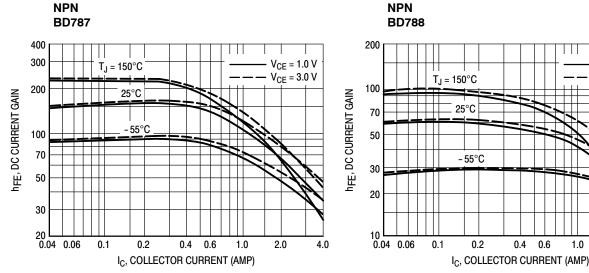


Figure 8. DC Current Gain

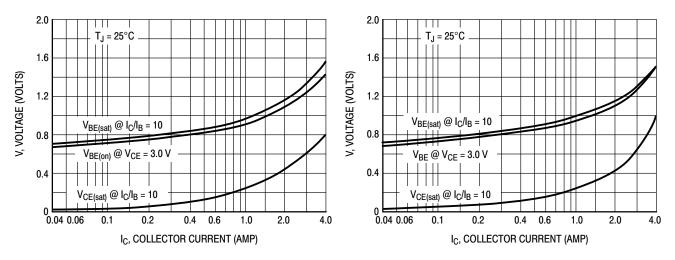


Figure 9. "On" Voltages

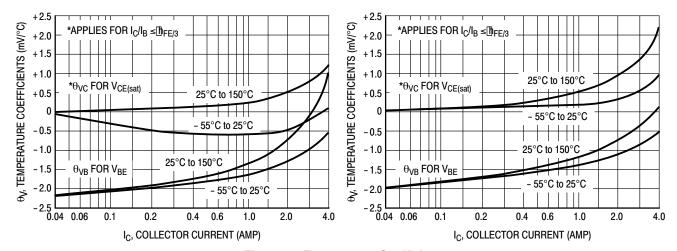
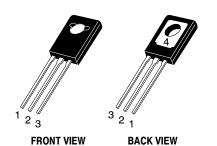


Figure 10. Temperature Coefficients

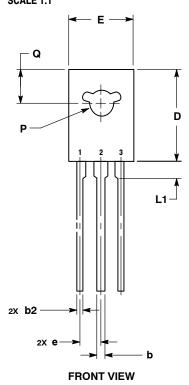


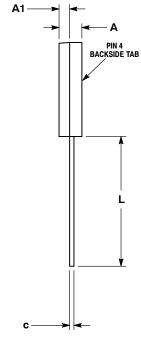


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DATE 25 MAR 2015

SCALE 1:1



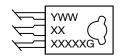


SIDE VIEW

- NOTES: 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994. 2. CONTROLLING DIMENSION: MILLIMETERS. 3. NUMBER AND SHAPE OF LUGS OPTIONAL.

	MILLIMETERS				
DIM	MIN	MAX			
Α	2.40	3.00			
A1	1.00	1.50			
b	0.60	0.90			
b2	0.51	0.88			
С	0.39	0.63			
D	10.60	11.10			
E	7.40	7.80			
е	2.04	2.54			
L	14.50	16.63			
L1	1.27	2.54			
P	2.90	3.30			
Q	3.80	4.20			

GENERIC MARKING DIAGRAM*



= Year ww

= Work Week XXXXX = Device Code = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

,	EMITTER COLLECTOR	2., 4.	CATHODE ANODE		COLLECTOR	2., 4.	ANODE 1 ANODE 2		MT 2
STYLE 6:	BASE	STYLE 7:	GATE	3. STYLE 8:	EMITTER	STYLE 9:	GATE	3. STYLE 10:	GATE
	CATHODE	PIN 1.			SOURCE	PIN 1.			SOURCE
	GATE ANODE	,	GATE MT 2		GATE DRAIN	2., 4.	DRAIN	,	DRAIN GATE

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